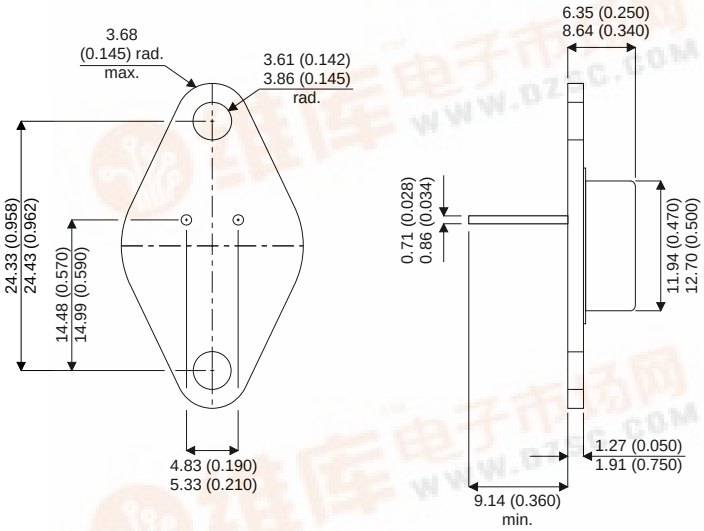
BDX14A

MECHANICAL DATA
Dimensions in mm



TO66 Package.

Pin 1 – Base Pin 2 – Emitter Case - Collector

PNP SILICON TRANSISTOR, EPITAXIAL BASE

FEATURES:
- LF Large Signal Power Amplification
- Medium Current Switching

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{CBO}	Collector – Base Voltage (Open Emitter)		- 90V
V_{CEO}	Collector – Emitter Voltage (Open Base)		- 55V
V_{CER}	Collector – Emitter Voltage	R_{BE} =100Ω	- 60V
V_{CEX}	Collector – Base Voltage	V_{BE} = +1.5V	- 90V
V_{EBO}	Emitter – Base Voltage		-7V
I_C	Collector Current		-4V
I_B	Base Current		-2V
P_{tot}	Power Dissipation		29W
T_J	Maximum Junction Temperature		200°C
T_{STG}	Storage Temperature		–65 to 200°C
$R_{th-(j-c)}$	Junction to Case.		6°C / W

SEME LAB

BDX14A

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CEX}	Collector Emitter Cut Off Current	V_{CE} = -90V	V_{BE} = +1.5V			-1	mA
		V_{CE} = -30V	V_{BE} = +1.5V T_{case} = 150°C			-5	
$V_{CEO(SUS)*}$	Collector Emitter Breakdown Voltage	I_C = -100mA	I_B = 0	-55			V
$V_{CER(SUS)*}$	Collector Emitter Breakdown Voltage	I_C = -100mA	R_{BE} = 100Ω	-60			
$V_{(BR)EBO*}$	Emitter Base Breakdown Voltage	I_E = -1A	I_C =0	-7			V
h_{21E}*	Static Forward Current Transfer Ratio	V_{CE} = - 4V	I_C = - 0.5A	25		250	—
$V_{CE(sat)*}$	Collector Emitter Saturation Voltage	I_C = - 0.5A	I_B = - 0.05A			-1	V
V_{BE*}	Base Emitter Voltage	V_{CE} = - 4V	I_C = - 0.5A			-1.7	V
f_T	Transition Frequency	V_{CB} = -10V f = 1MHz	I_C = - 0.2A	4			MHz

* Pulse test t_p = 300μs , δ < 2%